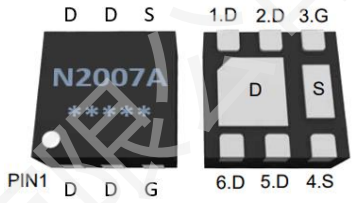
General Description:

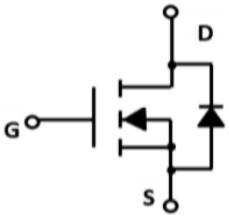
The LWN2007AD2 uses trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications. The package form is DFN2*2-6L, which accords with the ROHS standard and Halogen Free standard.

V_{DSS}	20	V
I_D	15	A
P_D	2.2	W
$R_{DS(ON)\ TYPE}$	4.0	mΩ

Marking and Pin Assignment



Inner Equivalent Principium Chart



Features:

- Fast Switching
- Low Gate Charge and $R_{DS(ON)}$
- Low Reverse transfer capacitances

Applications:

- DC-DC Converter
- Portable Equipment
- Power Management

100% DVDS Tested

100% Avalanche Tested

Package Marking and Ordering Information:

Marking	Part Number	Package	Packing	Qty.
N2007A/D.C.	LWN2007AD2	DFN2*2-6L	Reel	3000 Pcs

Absolute Maximum Ratings:

Symbol	Parameter		Value	Units
V_{DSS}	Drain-to-Source Voltage		20	V
I_D	Continuous Drain Current	T_A=25℃	15	A
	Continuous Drain Current	T_A=100℃	9.5	A
I_{DM}[a1]	Pulsed Drain Current		60	A
E_{AS}[a2]	Single pulse avalanche energy		110	mJ
V_{GS}	Gate-to-Source Voltage		±10	V
P_D	Power Dissipation		2.2	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range		150, -55 to 150	℃
T_L	Maximum Temperature for Soldering		260	℃

Thermal Characteristics:

Symbol	Parameter	Value	Units
$R_{\theta JA}$[a3]	Thermal Resistance, Junction-to-Ambient	57	℃/W

Electrical Characteristic (T_J = 25 °C, unless otherwise specified):

Static Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	20	--	--	V
I_{DSS}	Drain to Source Leakage Current	V_{DS}=20V, V_{GS}=0V	--	--	1.0	μA
$I_{GSS(F)}$	Gate to Source Forward Leakage	V_{GS}=+10V, V_{DS}=0V	--	--	100	nA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	V_{GS}=-10V, V_{DS}=0V	--	--	-100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	0.45	0.68	1.0	V
$R_{DS(ON)1}$	Drain-to-Source On-Resistance	V_{GS}=4.5V, I_D=15A	--	4.0	6.0	mΩ
$R_{DS(ON)2}$	Drain-to-Source On-Resistance	V_{GS}=2.5V, I_D=12A	--	5.2	7.5	mΩ

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
C_{iss}	Input Capacitance	V_{GS} =0V V_{DS} =10V f =1.0MHz	--	1827	--	pF
C_{oss}	Output Capacitance		--	297	--	
C_{rss}	Reverse Transfer Capacitance		--	273	--	
R_G	Gate resistance	V_{GS}=0V,V_{DS}=0V,f=1MHz	--	1.4	--	Ω

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	I_D =10A V_{DS} =10V V_{GS} =4.5V R_G =3.0Ω	--	30	--	ns
t_r	Rise Time		--	12	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	35	--	
t_f	Fall Time		--	21	--	
Q_g	Total Gate Charge	V_{GS} =4.5V V_{DS} =10V I_D =10A	--	27	--	nC
Q_{gs}	Gate to Source Charge		--	2.6	--	
Q_{gd}	Gate to Drain Charge		--	9.8	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Value			Units
			Min.	Typ.	Max.	
I_S	Diode Forward Current	T_A =25 °C	--	--	15	A
V_{SD}	Diode Forward Voltage	I_S=15A, V_{GS}=0V	--	--	1.2	V

a1：Repetitive rating; pulse width limited by maximum junction temperature

a2：V_{DD}=15V,L=0.1mH, R_G=25Ω, Starting T_j=25℃

a3：Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm^2 (one layer, 70 μm thick) copper area for drain connection.

Characteristics Curve：

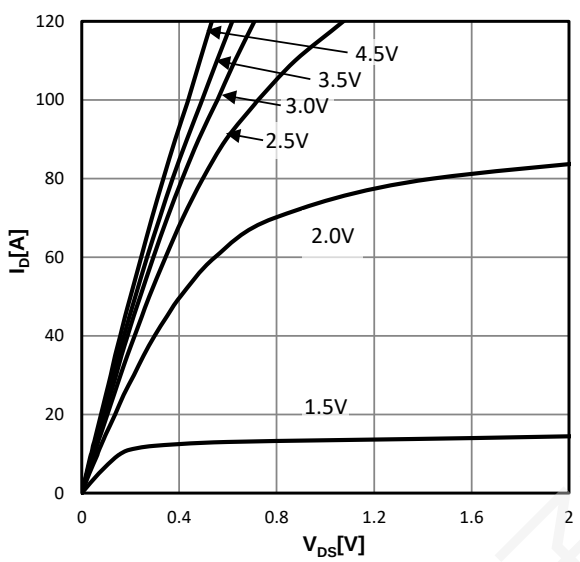
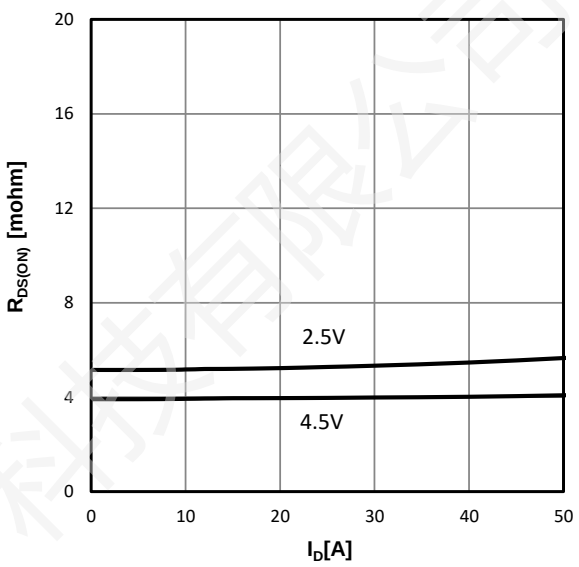
Figure 1: Typ. output characteristics	Figure 2: Typ. drain-source on resistance
	
$I_D=f(V_{DS})$, T_j=25 °C; parameter: V_{GS}	$R_{DS(on)}=f(I_D)$, T_j=25 °C; parameter: V_{GS}

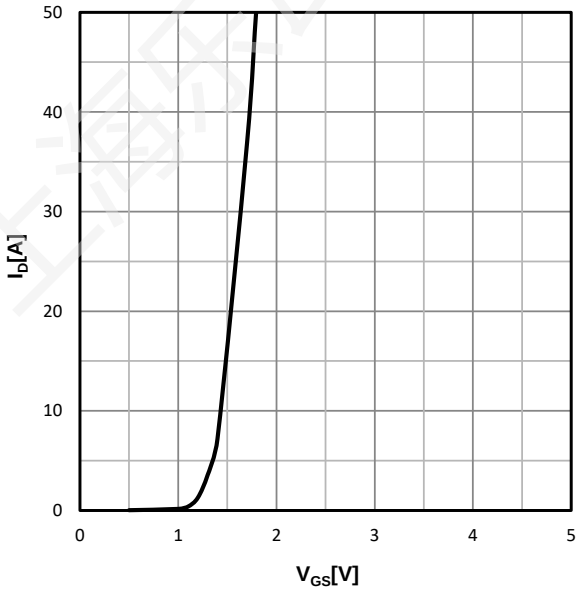
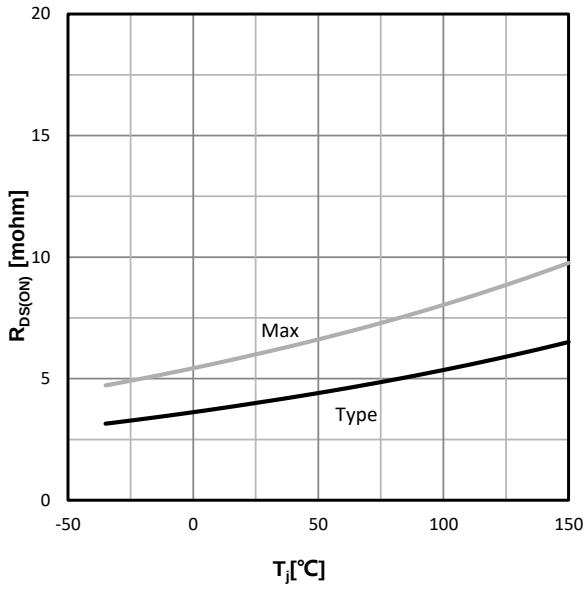
Figure 3: Typ. transfer characteristics	Figure 4: drain-source on resistance
	
$I_D=f(V_{GS})$, $\|V_{DS}\|>2\|I_D\|R_{DS}(on)max$;	$R_{DS(on)}=f(T_j)$, I_D=15A, V_{GS}=4.5V;

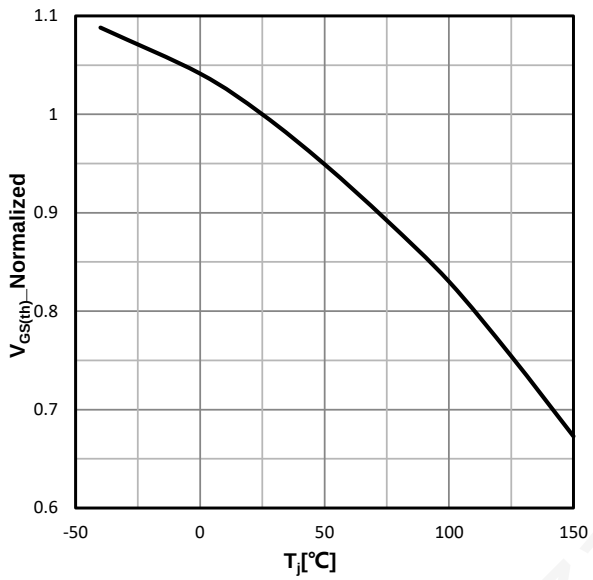
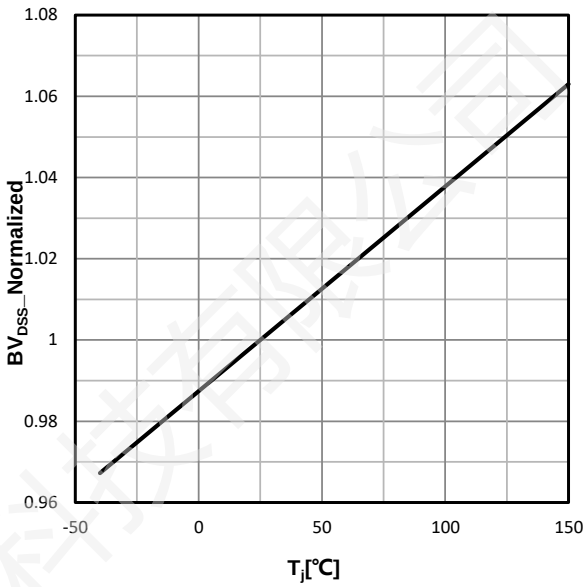
Figure 5: Typ. gate threshold voltage	Figure 6: Drain-source breakdown voltage
	
$V_{GS}=f(T_j)$,I $V_{GS}=V_{DS,}I_D=250\mu A$;	$V_{BR(DSS)}=f(T_j)$; $I_D=250\mu A$;

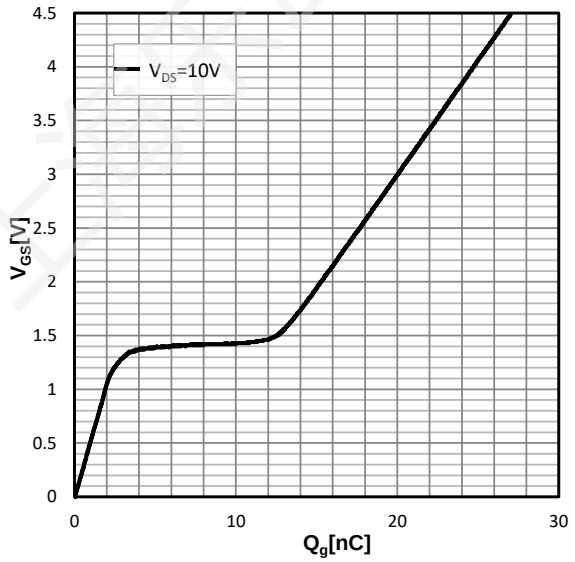
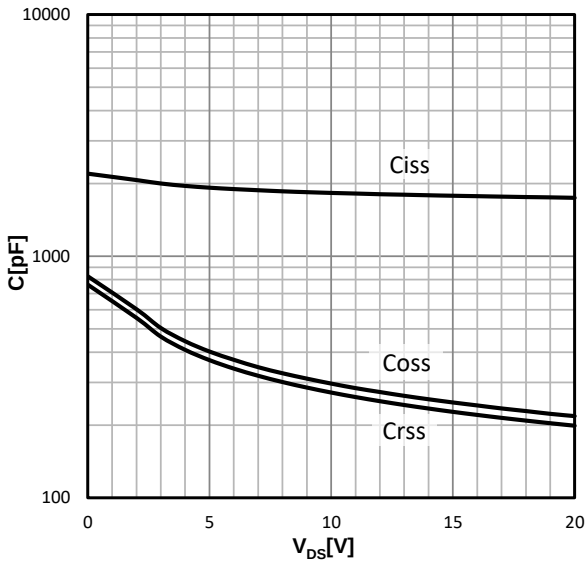
Figure 7: Typ. gate charge	Figure 8: Typ. Capacitances
	
$V_{GS}=f(Q_g)$, $I_D=10A$, $T_j=25$ °C; parameter: V_{DS}	$C=f(V_{DS})$; $V_{GS}=0V$; f=1.0 MHz;

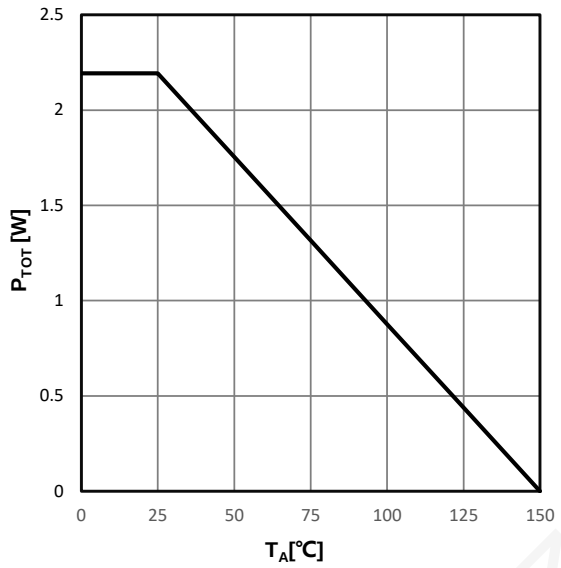
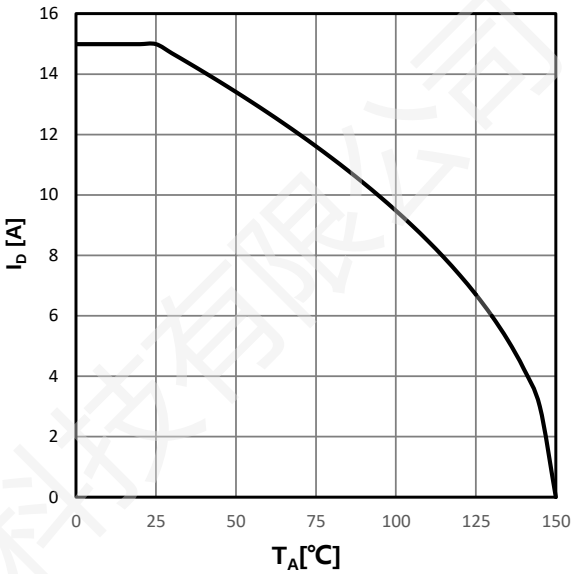
Figure 9: Power dissipation	Figure 10:Drain current
	
$P_{tot}=f(T_A)$;	$I_D=f(T_A)$;

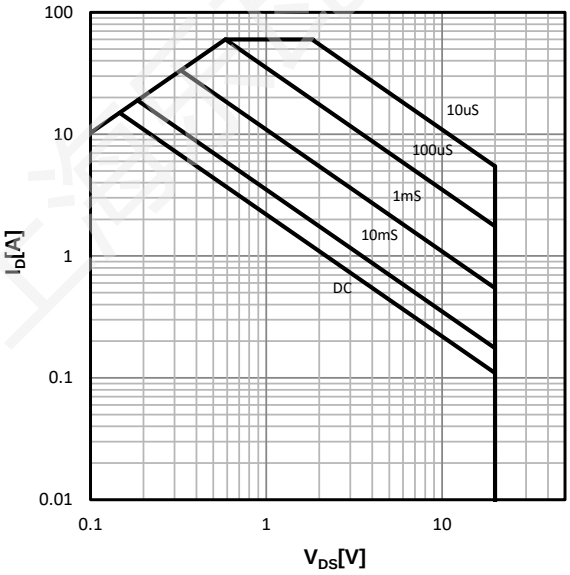
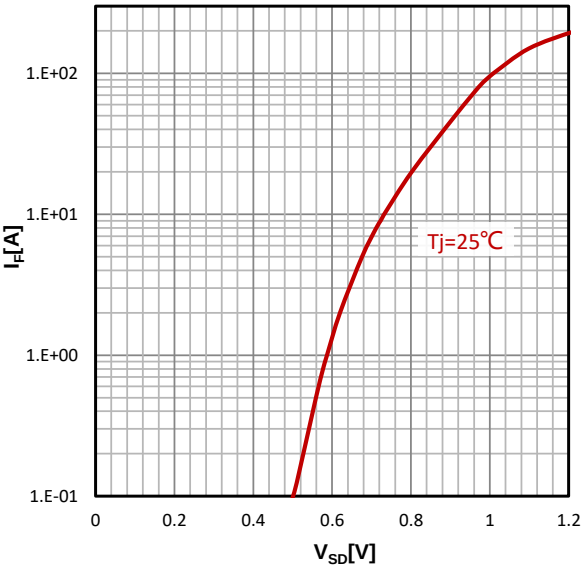
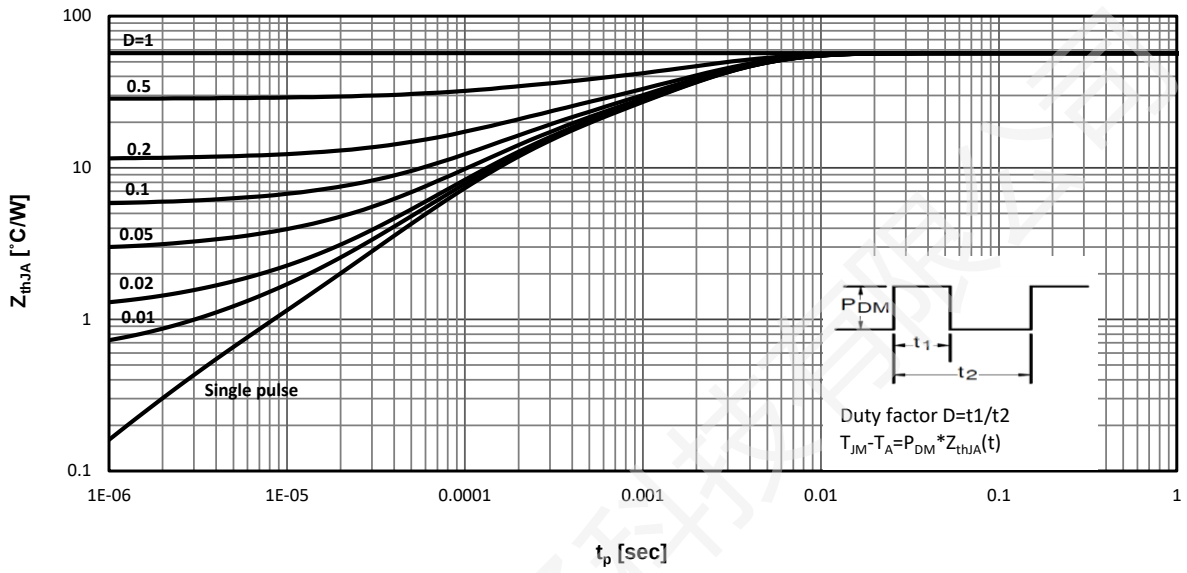
Figure 11: Safe operating area	Figure 12: Typ. forward characteristics
	
$I_D=f(V_{DS})$; T_A=25 °C; D=0; parameter: tp	$I_F=f(V_{SD})$;

Figure 13: Max. Transient Thermal Impedance



$Z_{thJA}=f(t_p)$; parameter: D

Test Circuit & Waveform:

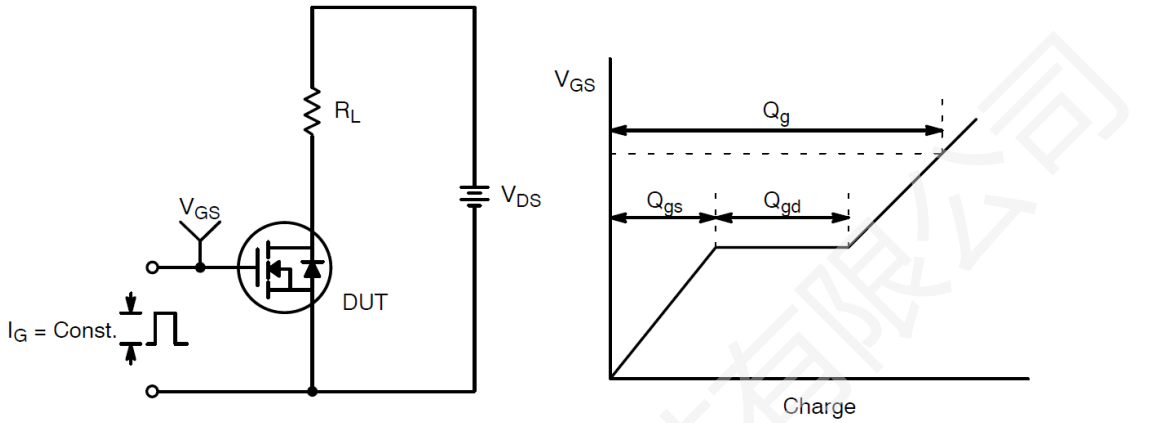


Figure 14: Gate Charge Test Circuit & Waveform

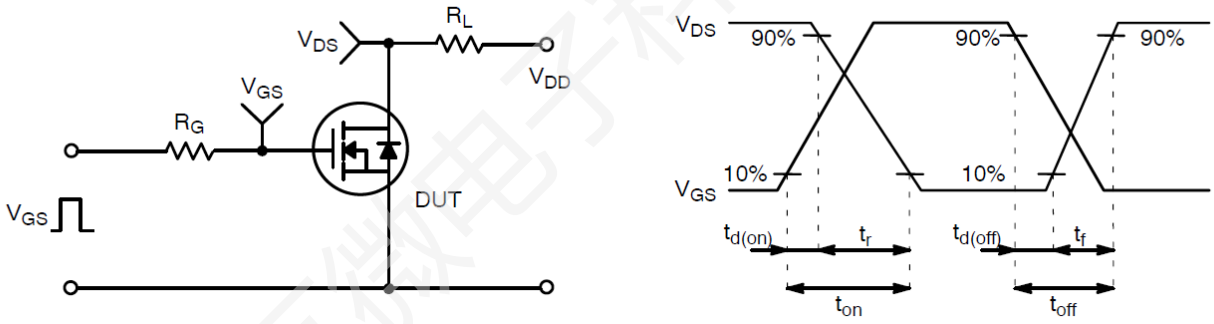


Figure 15: Resistive Switching Test Circuit & Waveforms

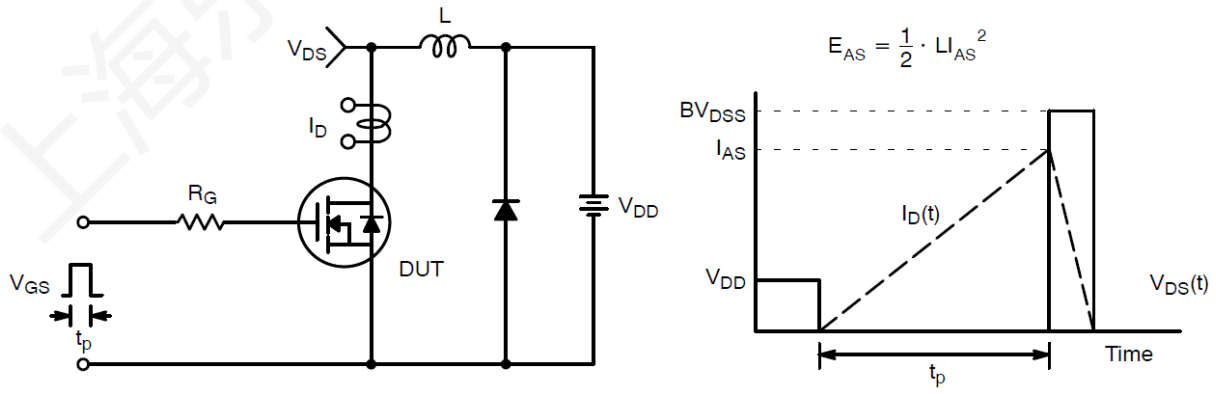
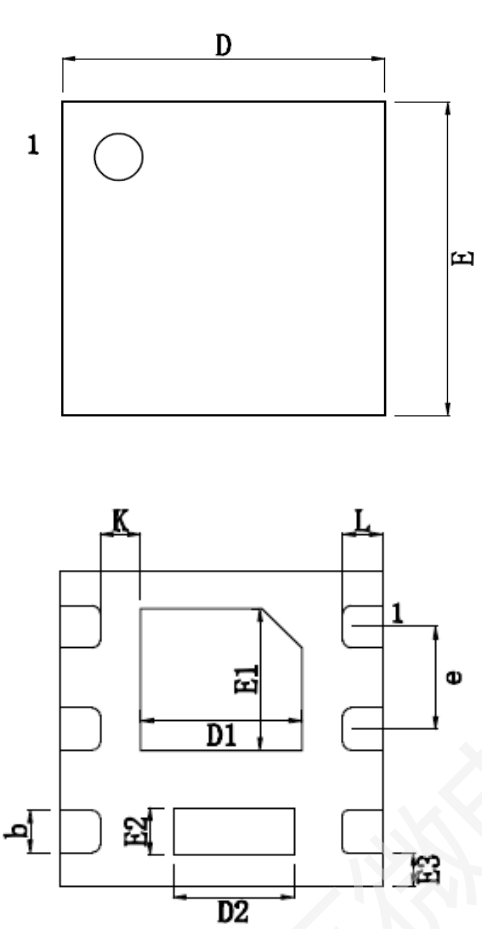


Figure 16: Unclamped Inductive Switching Test Circuit & Waveforms

Package Outline:



SYMBOL	MILIMETER		
	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0.00	——	0.05
b	0.22	0.29	0.35
c	0.203 TYP		
D	1.95	2.00	2.05
D1	0.90	1.00	1.10
D2	0.55	0.70	0.85
E	1.95	2.00	2.05
E1	0.80	0.90	1.00
E2	0.25	0.30	0.35
E3	0.215 REF		
e	0.65 BSC		
K	0.25 REF		
L	0.20	0.25	0.30

Revision History:

Revison	Date	Descriptions
Rev 1.1	July.2025	Initial Version

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